

# A radiation-tolerant Point-Of-Load buck DC-DC converter ASIC DC-DC for LHC upgrades

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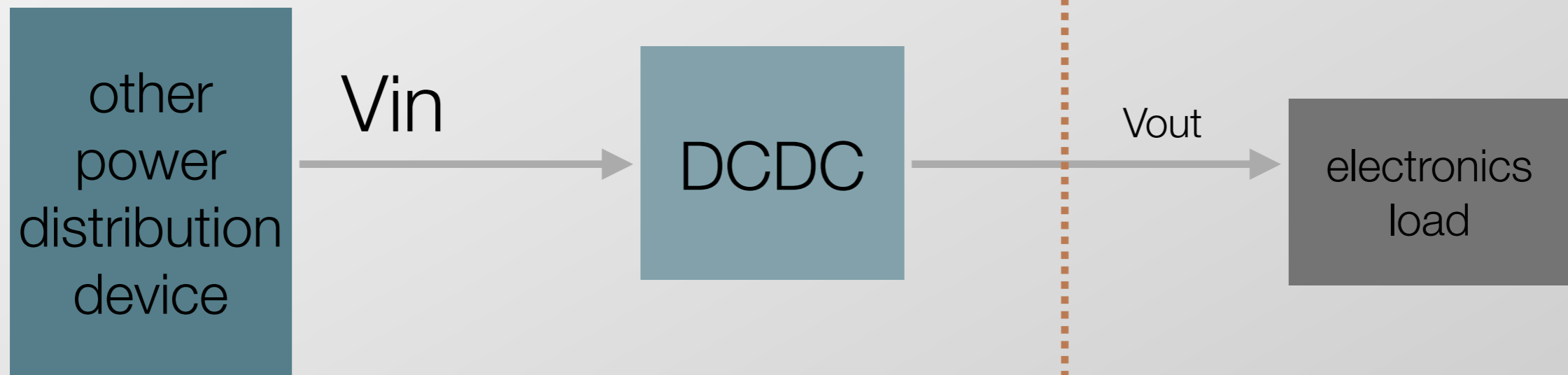
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# What is a POL DCDC converter

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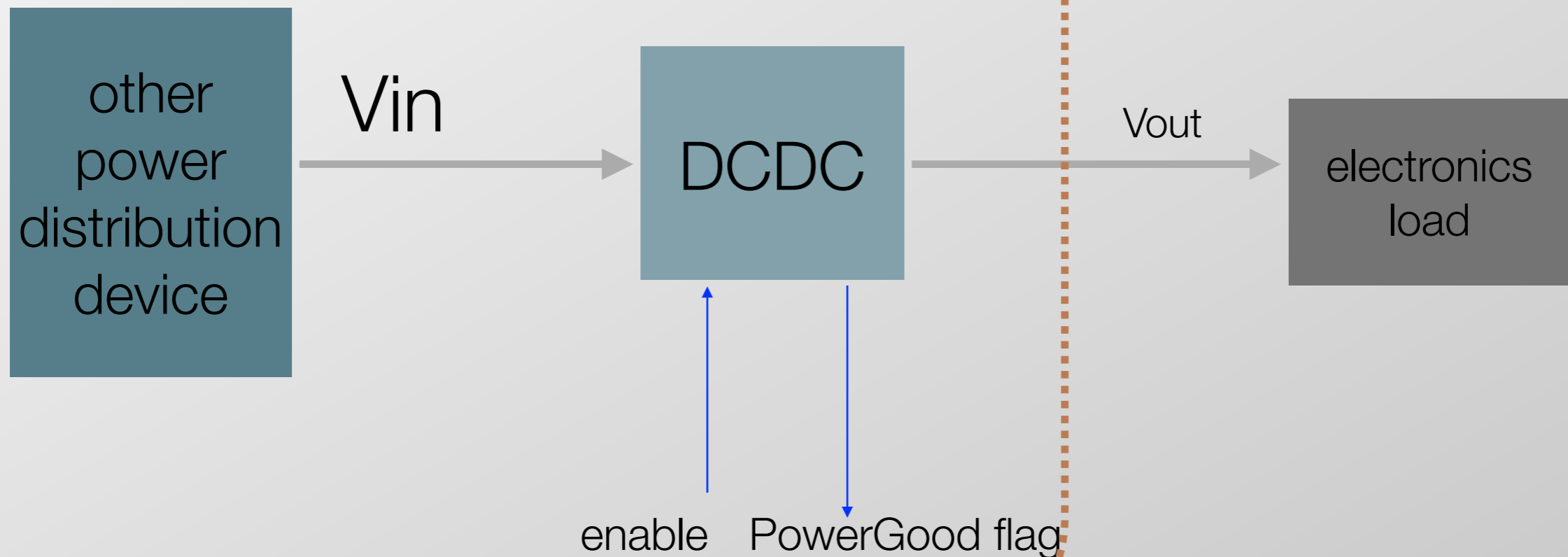
## Power distribution network



# What is a POL DCDC converter

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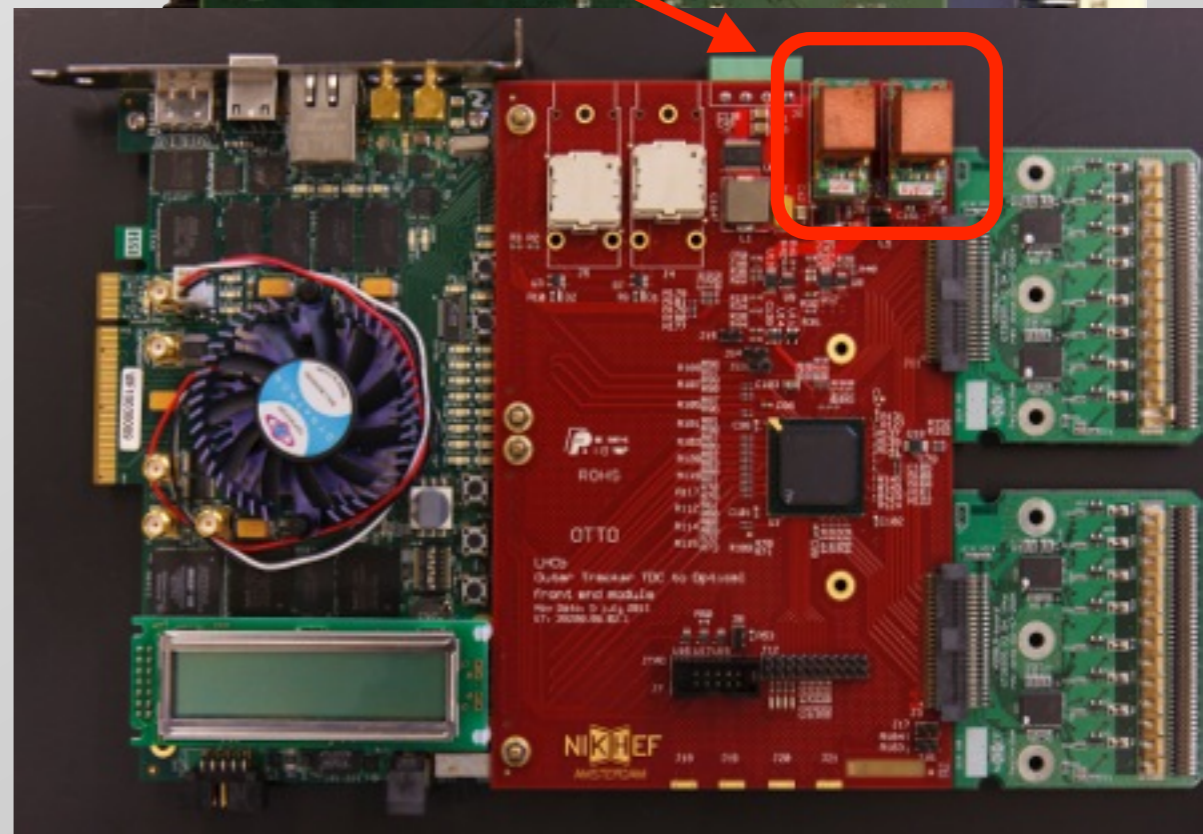
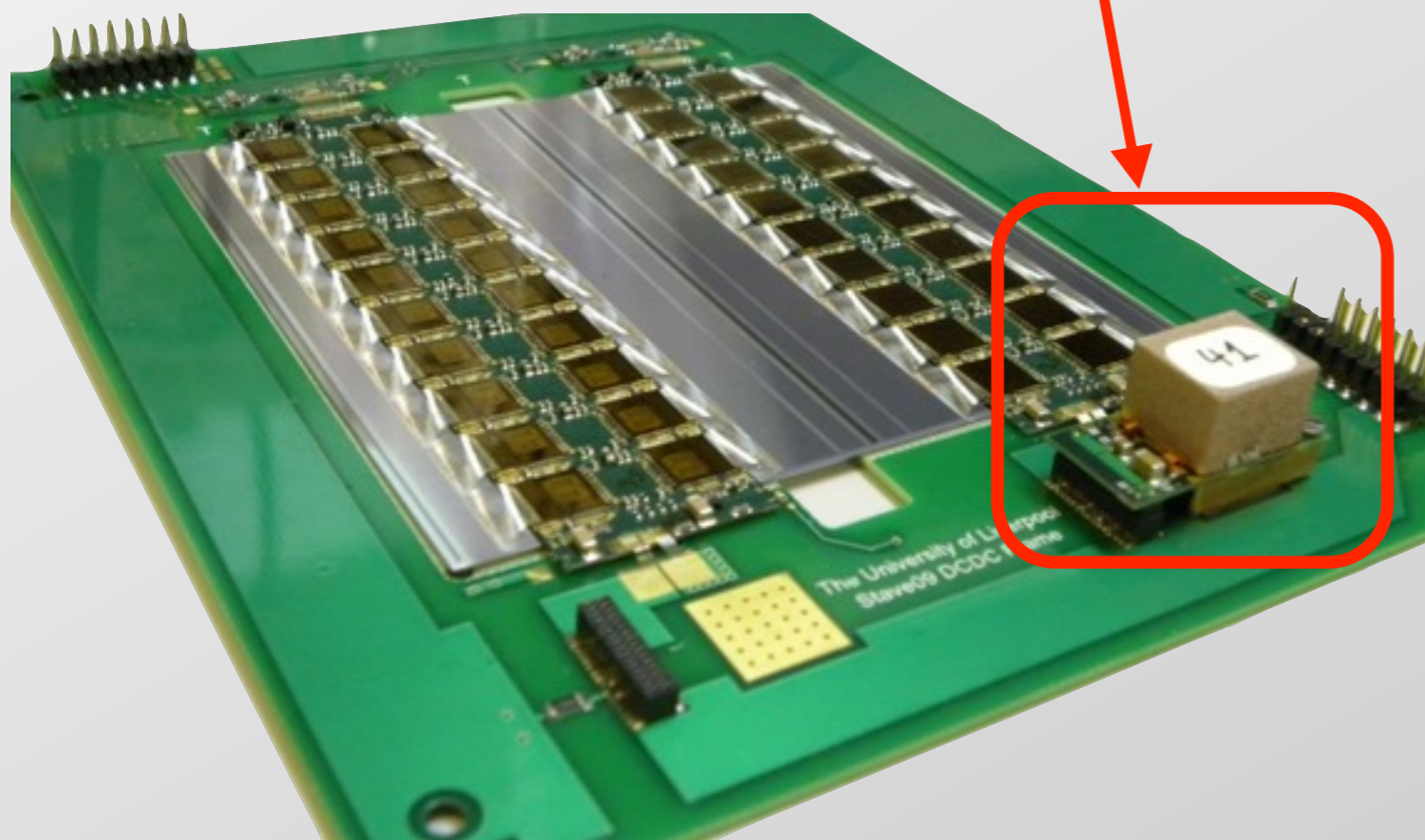
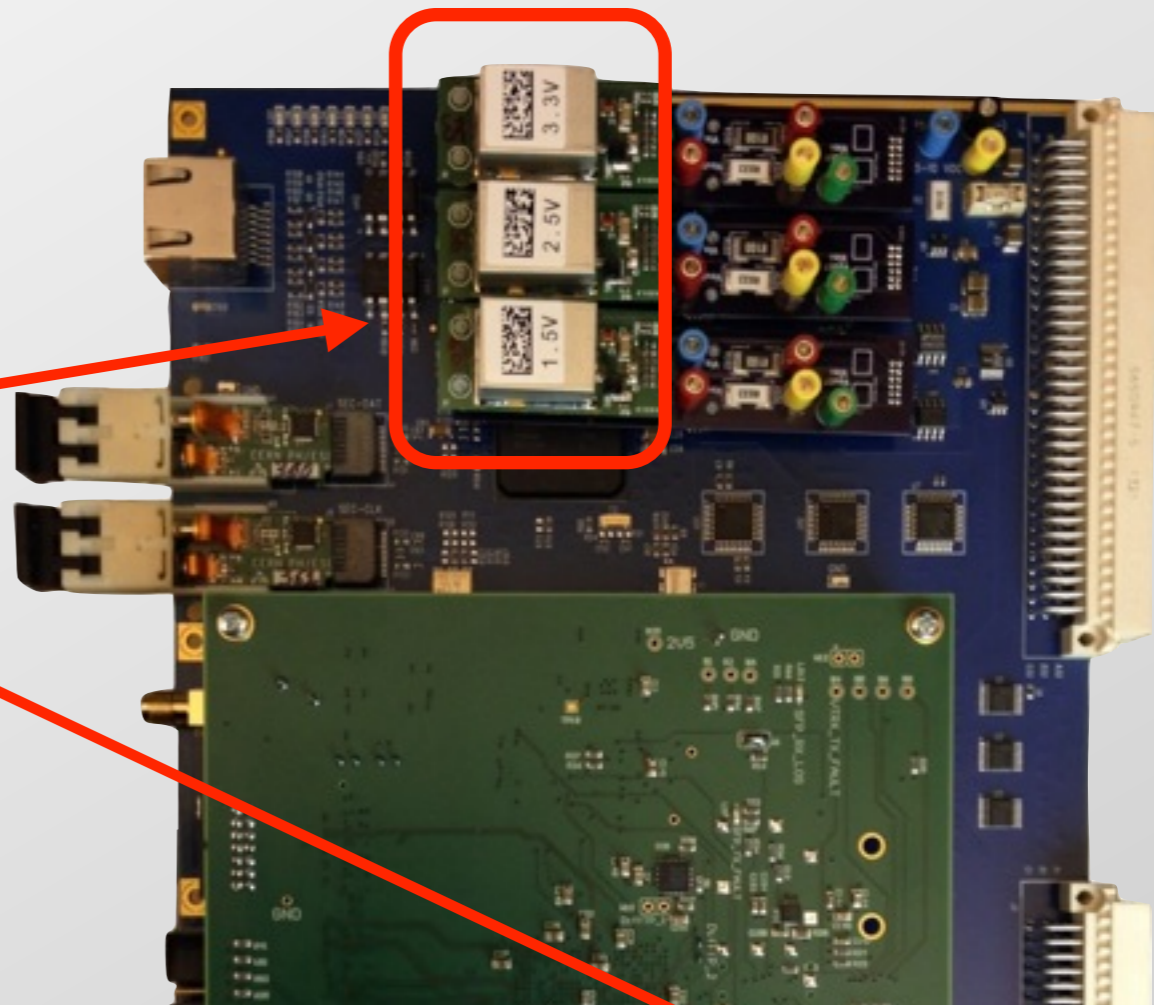
## Power distribution network



# Complete plug-in DCDC module

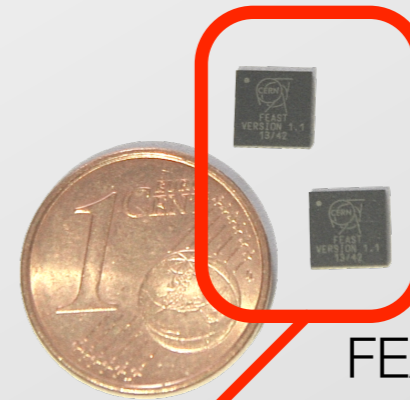
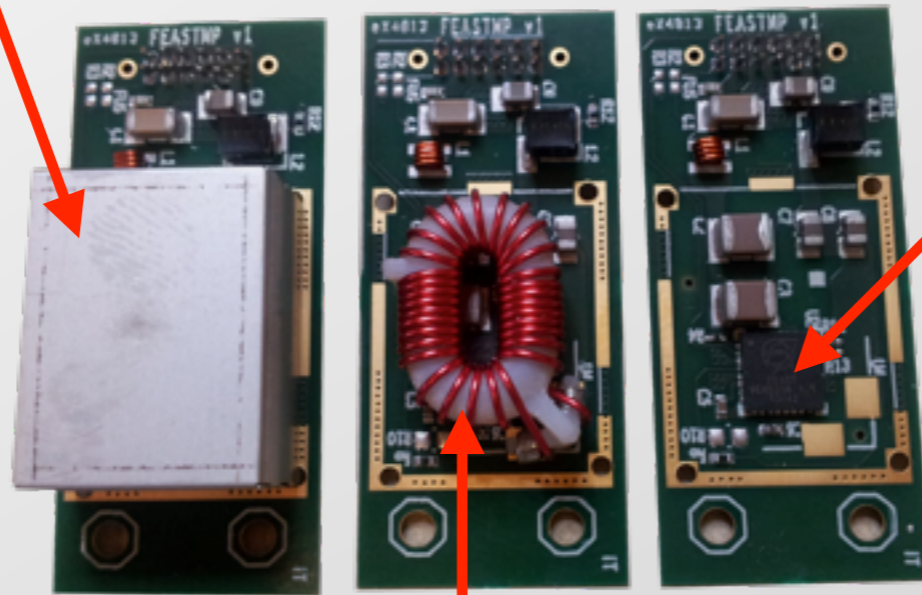


- Radiation tolerant
- Magnetic field tolerant to 40,000 Gauss
- Low noise
- Small volume and footprint



Cu shield

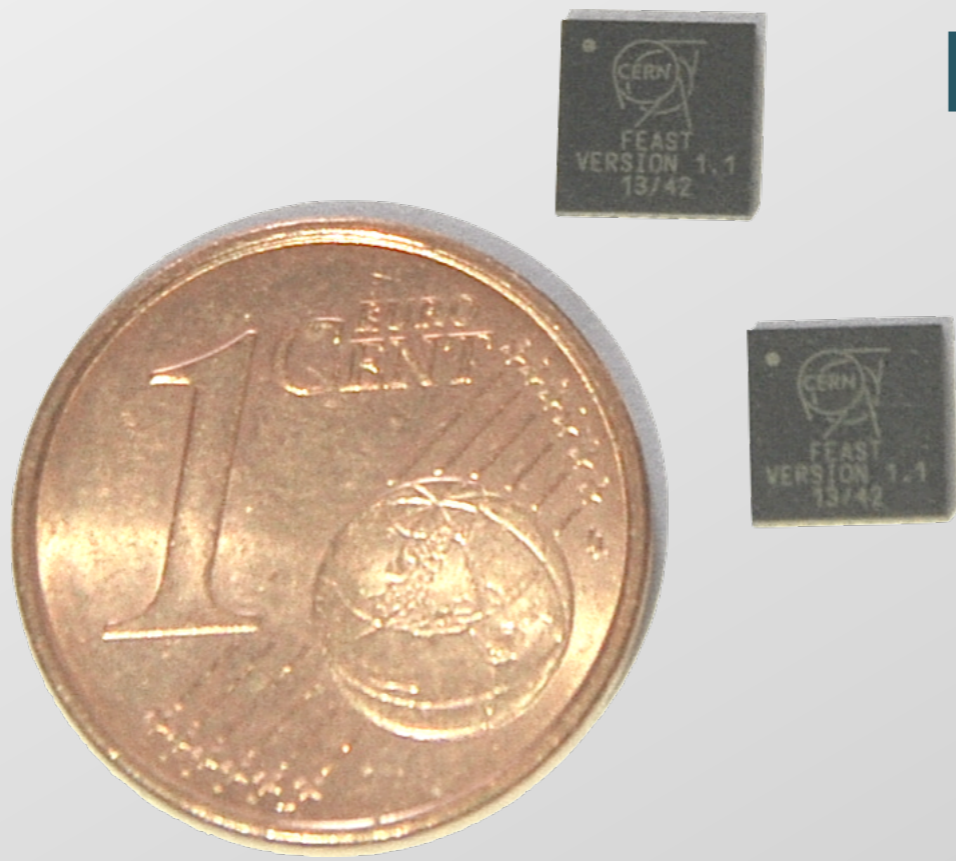
### FEASTMP module



FEAST2 ASIC



Custom air-core toroid inductor, 400nH



# FEAST2

# Outline: the FEAST2 ASIC

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- Requirements
- Approach to achieve radiation tolerance
- Radiation test results

# Requirements for the ASIC

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- Constraints:

- ▶ air-core inductor → ▶ switching frequency of 1-3MHz
- ▶ 12V input voltage → ▶ adequate CMOS technology
- ▶ radiation tolerant → ▶ adequate CMOS technology and design provisions
- ▶ small → ▶ simple architecture, reduced number of passives (maximum integration)  
BUCK TOPOLOGY

- Relaxed constraints:

- ▶ standby consumption → ▶ consumption of control circuits almost irrelevant



# FEAST2 in a nutshell

	parameters	value	notes
Main electrical parameters	Input Voltage ( $V_{in}$ )	5 V - 12 V	
	Output Voltage ( $V_{out}$ )	0.6 V - 5 V	
	Output current ( $I_{out}$ )	0 - 4 A	
	Maximum output power ( $P_{out}$ )	10 W	Cooling required
	Programmable Switching frequency	1-3 MHz	Recommended: 1.8 MHz
	Inductor value	0.15 – 1.5 $\mu$ H	Optimum: 400-500 nH
	Line regulation, 6 – 12 V range	5 mV	Measured at $V_{out} = 1.2V$ and 2.5V at the output pins of the packaged ASIC
	Load regulation, 1 – 4 A range	5 mV	
Protection features	Over Current protection peak level	6 A	Corresponding to 4.8 A average for 1.8MHz, 400nH
	Over Temperature protection threshold	103 °C	Hysteresis of 40°C
	Under Voltage lockout	4.5 V	Minimum input voltage for operation
	Soft-Start duration	470 us	To limit inrush currents
Control	Enable (input) threshold	815 mV	Compatible with CMOS logic 1 – 3.3 V
	Range around nominal $V_{out}$ for Pgood signal to be asserted	$\pm 6.5\%$	Open drain output

# Approach to achieve radiation tolerance

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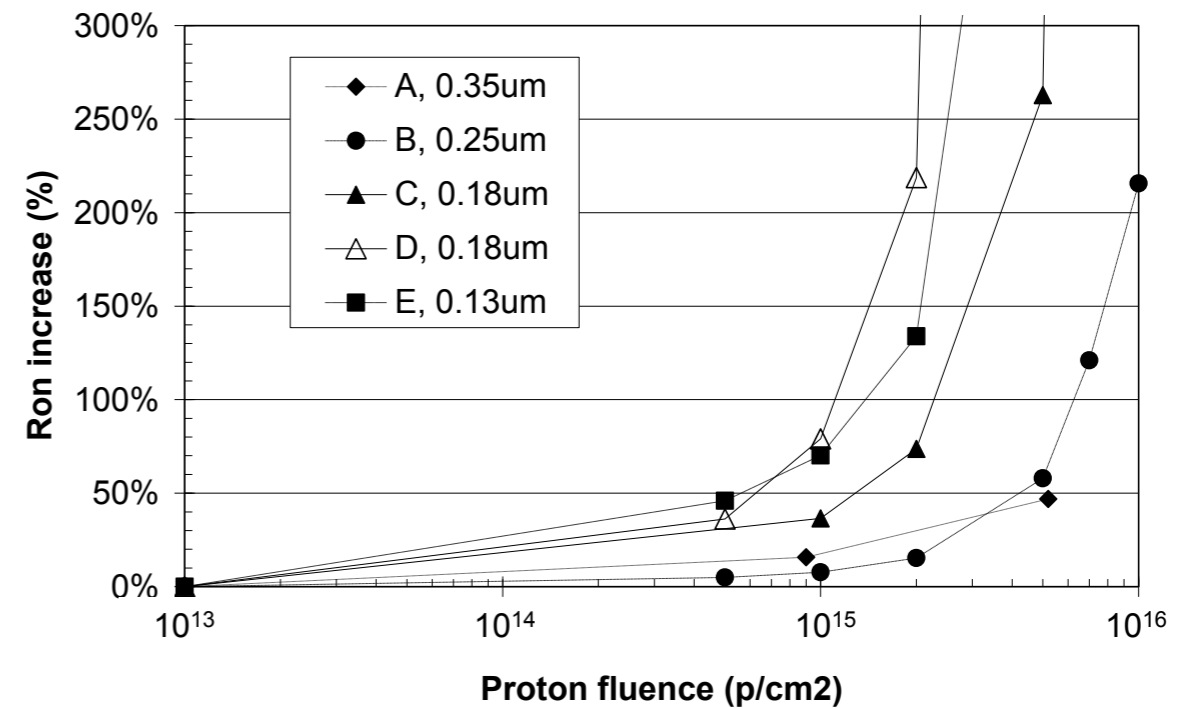
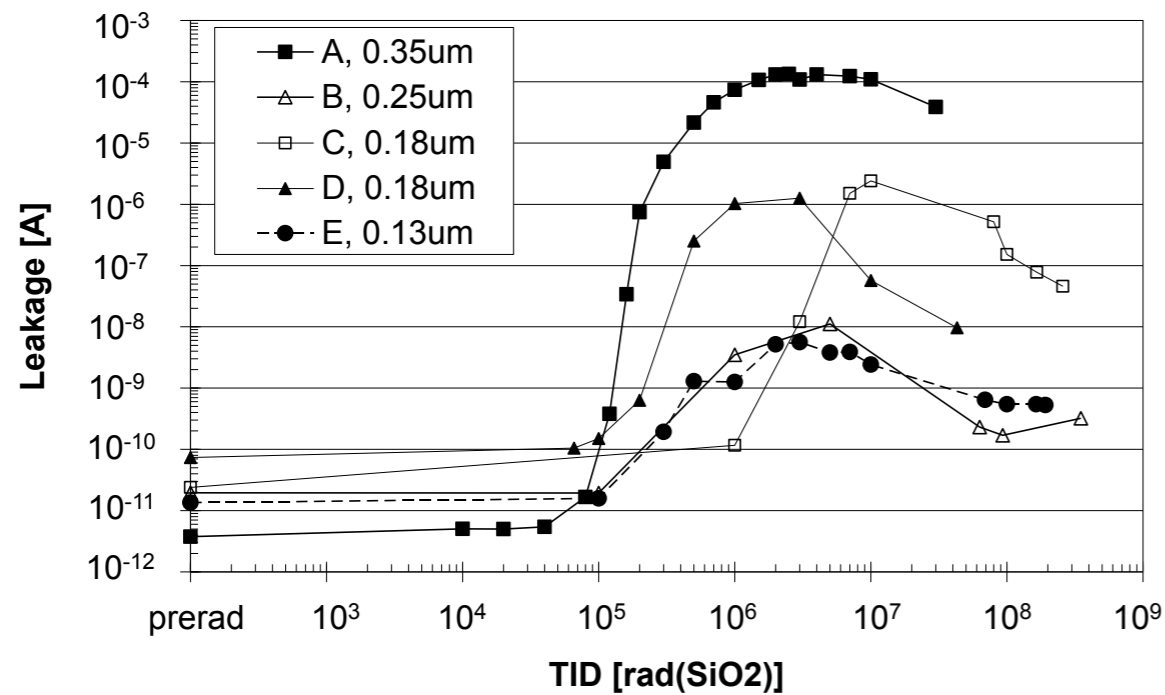
1. CMOS technology with high-voltage module (LDMOS) to be chosen after survey of available technologies and testing for the all radiation effects
2. Systematic use of Hardness-By-Design (HBD) techniques for TID and SEEs

# Technology choice

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- 5 suitable technologies selected and radiation tested for TID and DD (technology node range: 0.35-0.13um)
  - ‘high voltage’ LDMOS were critical - no custom layout modification possible
  - the biggest concern came from DD (leakage current in LDMOS can be made irrelevant in the design of the ASIC)

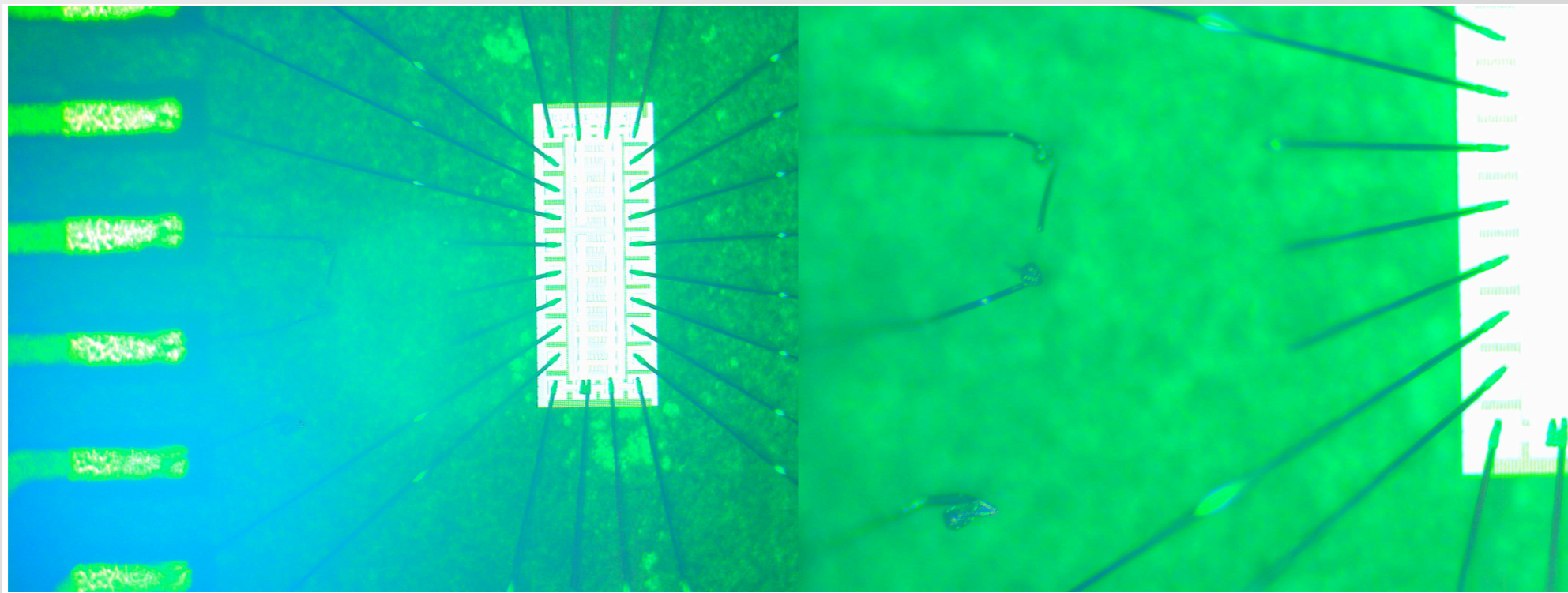
# Example TID/DD radiation effects on LDMOS



# Example of SEB sensitivity

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- LDMOS from 3 technologies also tested for SEB/SEGR sensitivity
  - NMOS in one of them were sensitive to SEB below 10V and below a LET of  $10\text{MeVcm}^2\text{mg}^{-1}$



Molten wire-bonds after a SEB

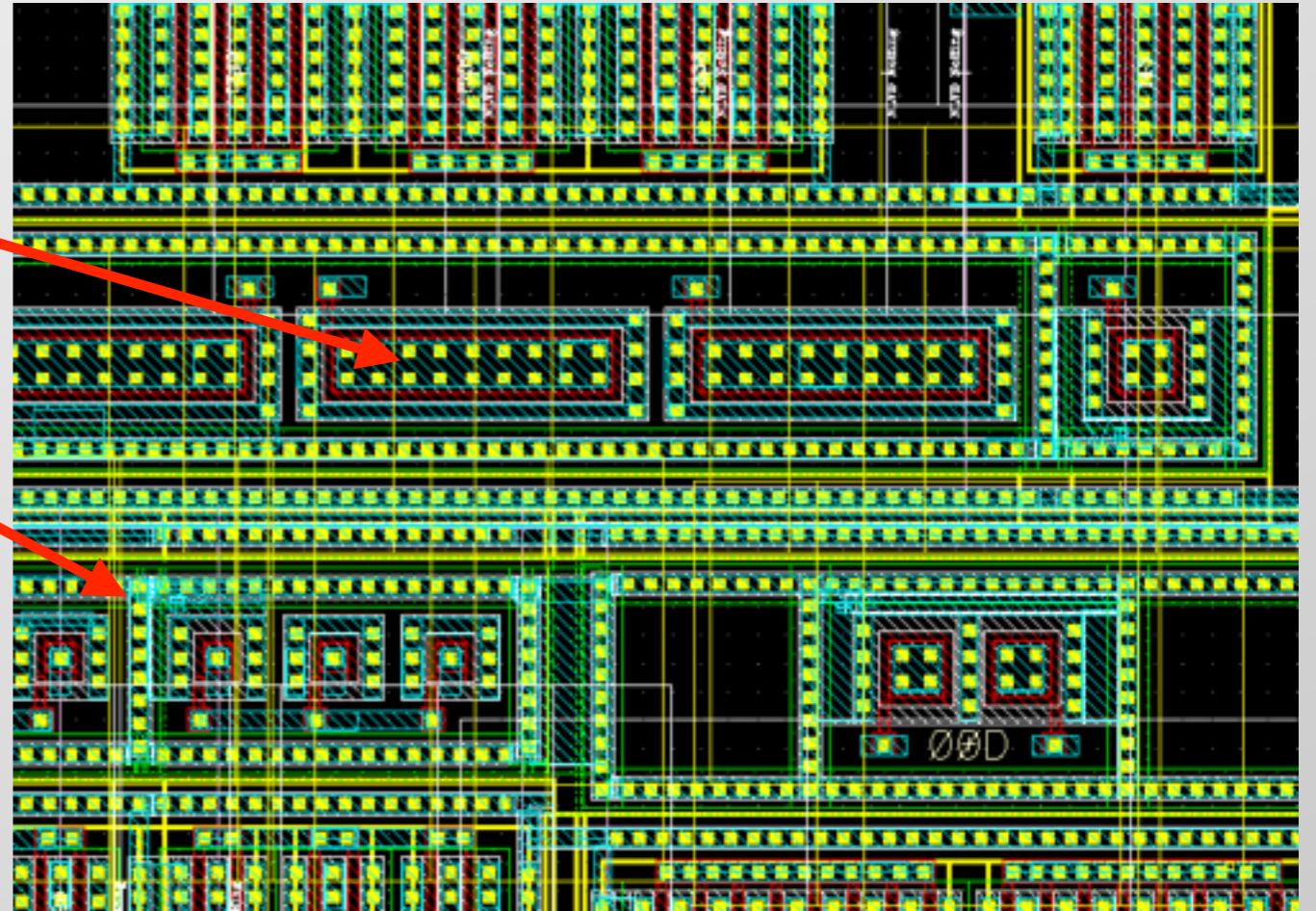
# Technology choice

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- Combination of TID, DD and SEB/SEGR tests led to the choice of the technology:
  - 0.35um CMOS with high voltage module
    - it offers a good palette of devices for analog design
    - it features a large number of high-voltage transistors, and complete isolation from the substrate up to 80V
    - easily accessible for MPW, engineering and production runs, and reasonable cost

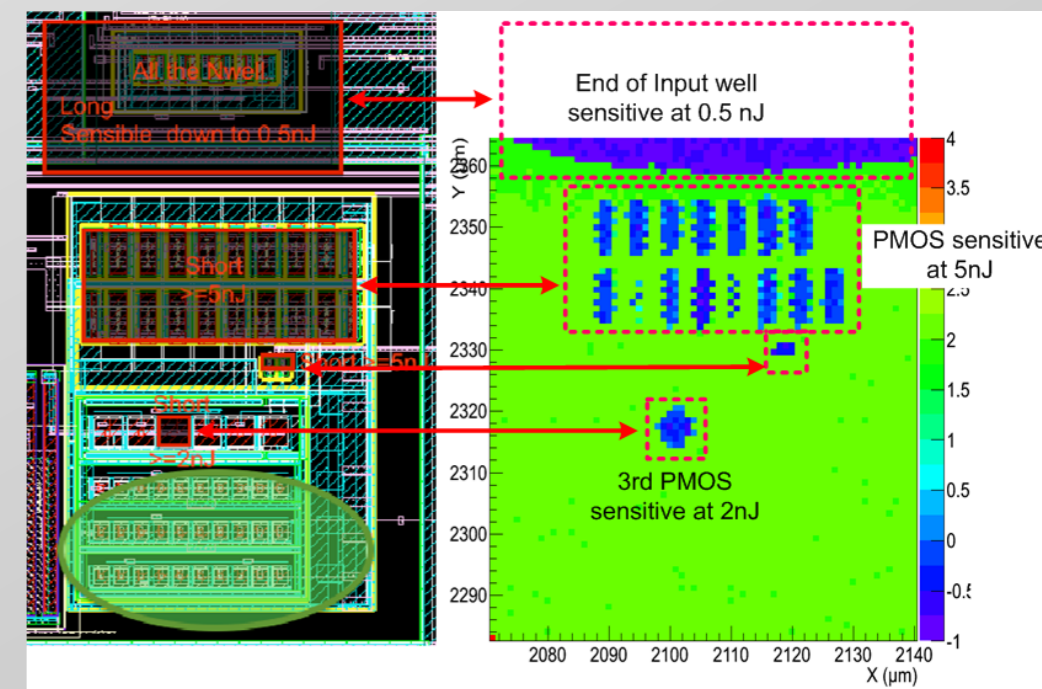
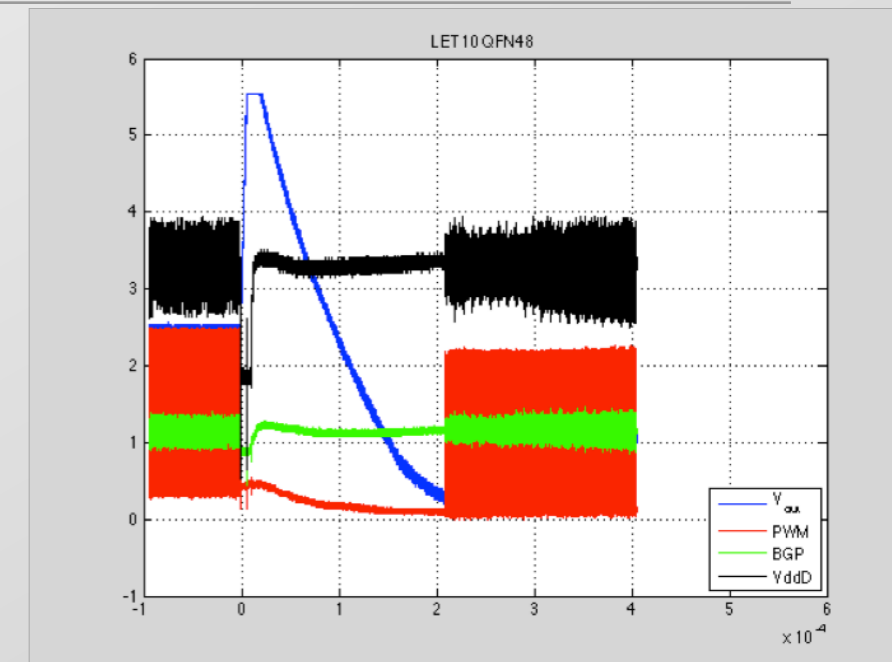
# HBD techniques: TID

- Enclosed Layout Transistors (ELTs) for all NMOS
- Systematic use of p+ guard-rings
- TID tolerance OK as from first prototype integration



# HBD techniques: SEE

- SEE testing performed on several generations of prototypes, with Heavy Ions and protons
  - removal of all sensitivities to SEEs was not easy. Some were difficult to foresee, for others Spice simulations were even misleading
    - observed consequences included the restart of the ASIC or the temporary loss of functionality with a large transient above the nominal output voltage
  - use of pulsed laser to fully map the sensitive points was a very precious tool (test done at Pulscan, Gradignan, France)
- Design techniques systematically used:
  - Triplication & voting used in most sensitive functions
  - Analog nodes protected by increase of currents and load capacitance

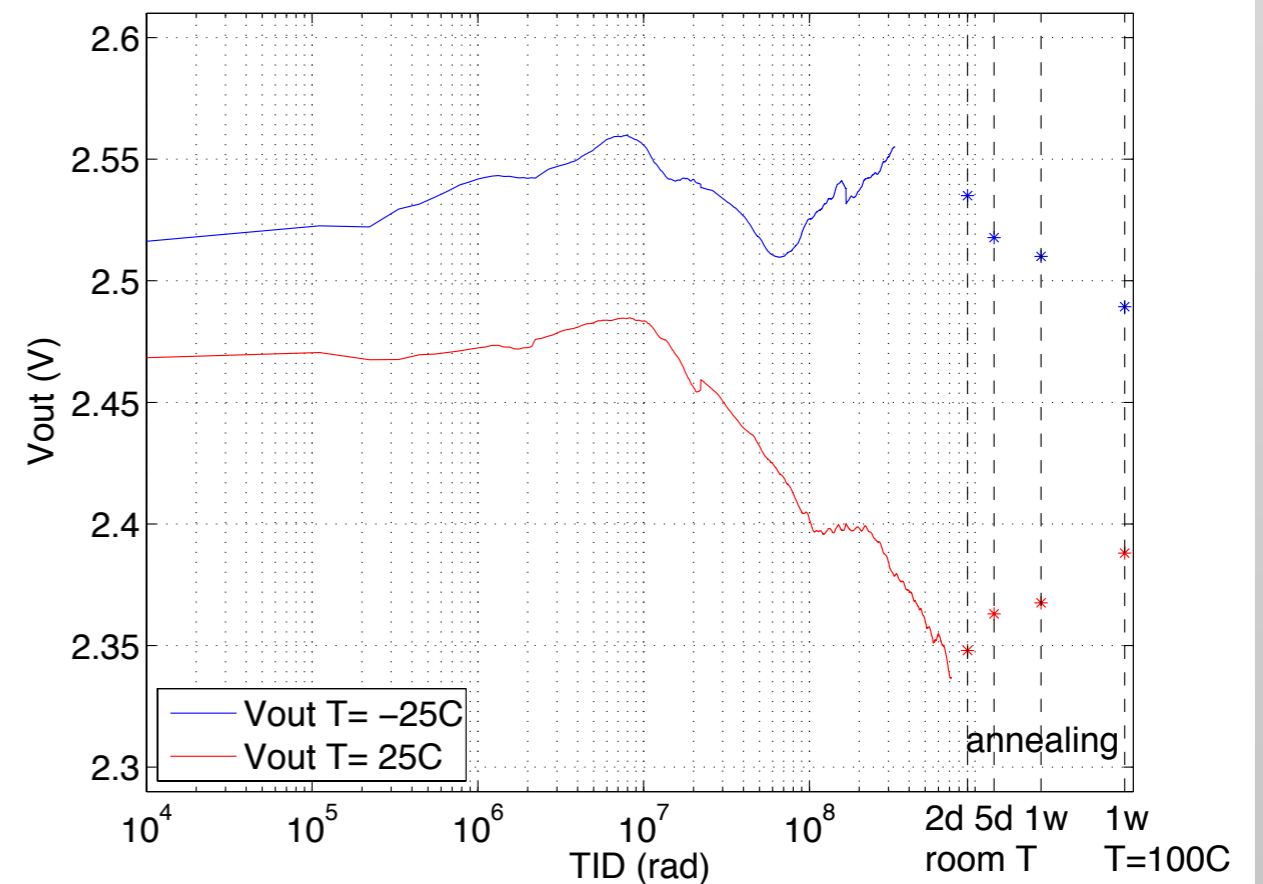
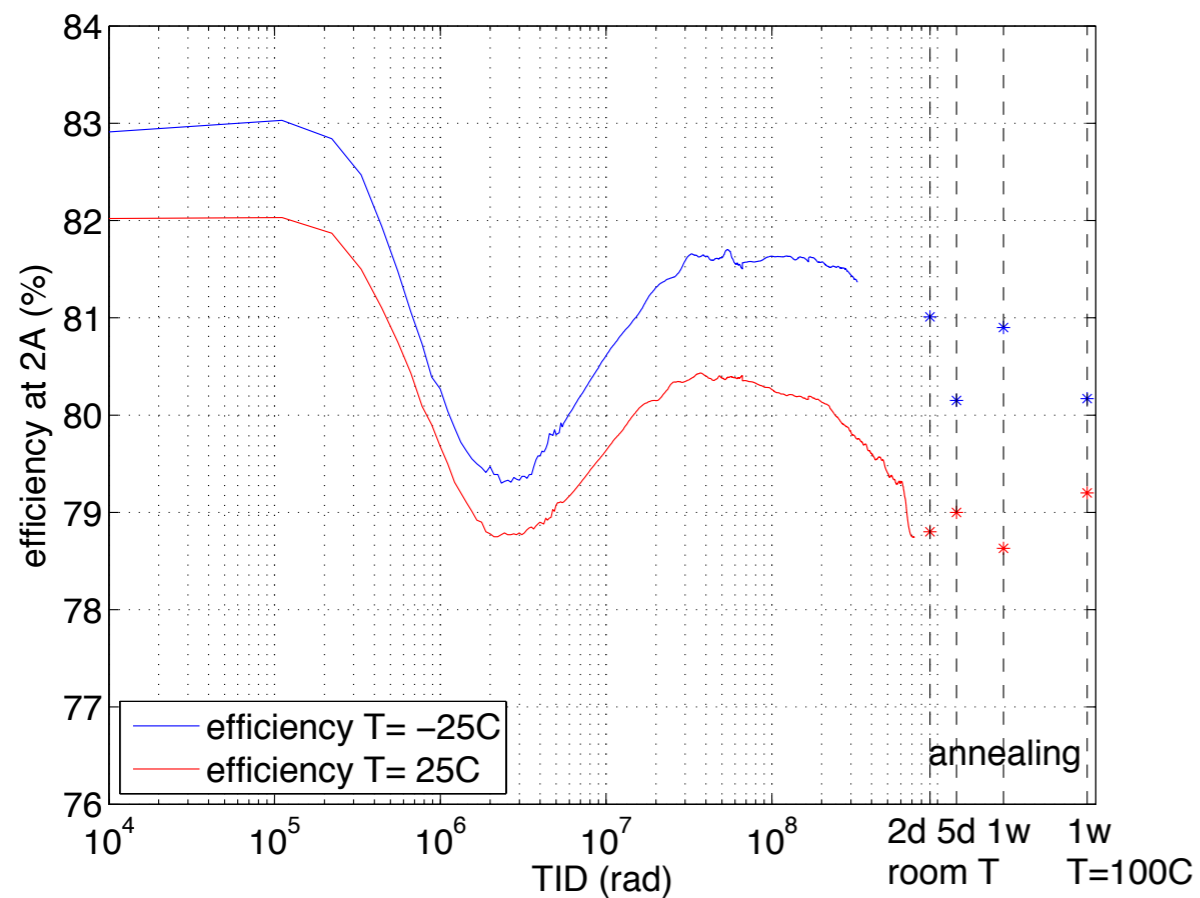




Radiation test results

# Radiation test results: TID

- All irradiated samples were constantly functional during irradiation and annealing. Typical maximum TID reached in the test: 200-700Mrad



# Radiation test results: DD

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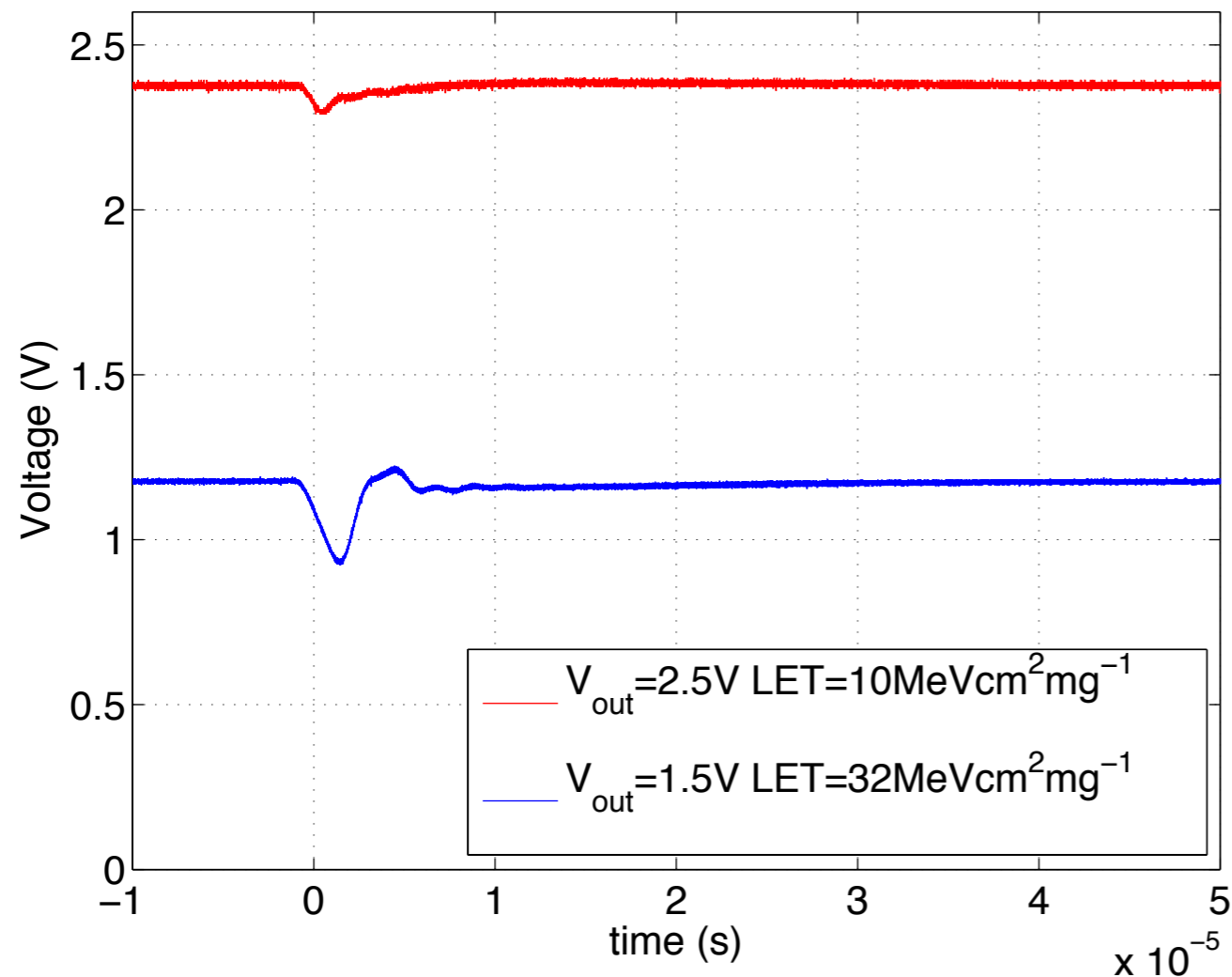
- Functionality is lost after an integrated flux of  $5 \times 10^{14}$  n/cm<sup>2</sup> (1 MeV equivalent). This is due to damage to p-channel LDMOS transistors used in the on-chip linear voltage regulators
- The reference voltage generator shifts with the integrated flux, and as a consequence the output voltage increases. This starts to appear at the level of  $10^{14}$  n/cm<sup>2</sup>

# Radiation test results: SEEs

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- Tests performed with the ASIC regulating a voltage (1.5 or 2.5V typically) on a 1-2A load
- Heavy Ions in HIF, CRC, Louvain-la-Neuve
  - FEAST2 continuously provides regulated power to the load during the full test (total integrated flux =  $126 \times 10^6$  ions/cm<sup>2</sup> at different LET up to 65MeVcm<sup>2</sup>mg<sup>-1</sup>). No reset, no SEFI observed
  - Short (<2-3us) and small (<20%) transients on the output are observed. These are irrelevant for the application

# SETs observed during HI irradiation

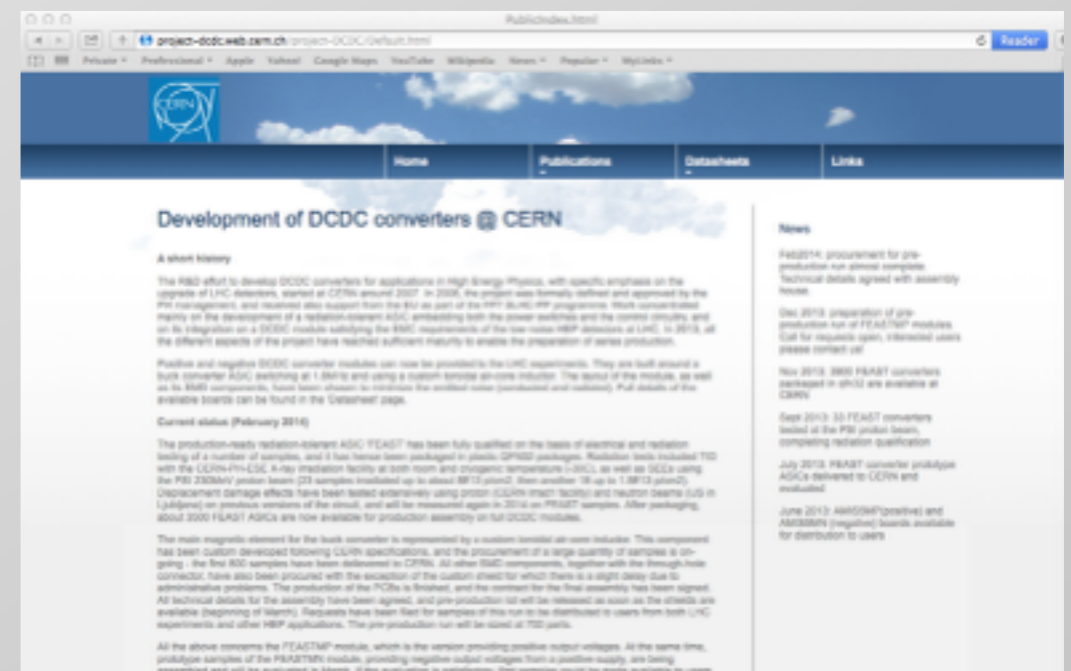


Example SETs observed during HI irradiation. Amplitude increases with the LET of the incident particles, but it is always below 20% of the nominal  $V_{out}$ . Typical duration is below 2 $\mu$ s

# Summary

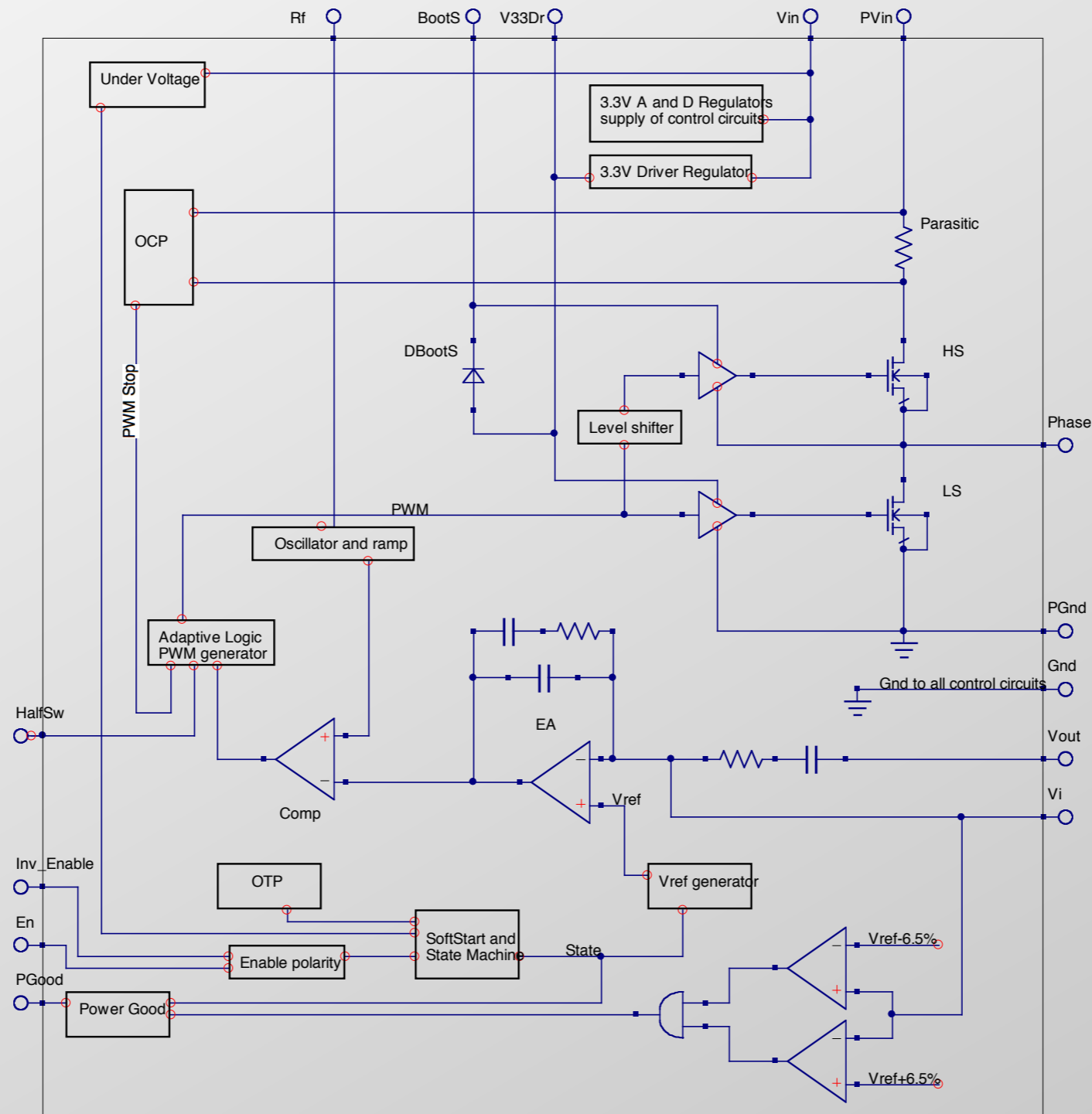
- FEAST2 is the final product of a long R&D effort. It is now qualified for all radiation effects
- The circuit is available in packaged form (QFN32) for LHC experimental groups, and as full plug-in module (FEASTMP). It is in production, with 1000 modules being tested at CERN this week
- Information and datasheet available in our public web page

<http://project-dcdc.web.cern.ch>



Spare Slides

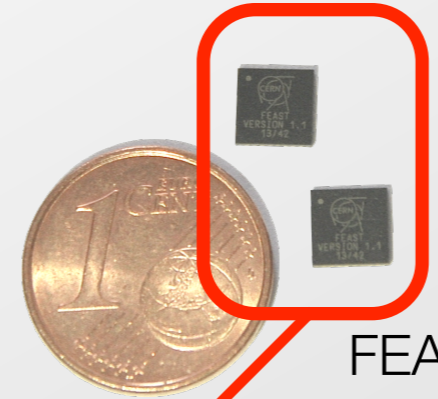
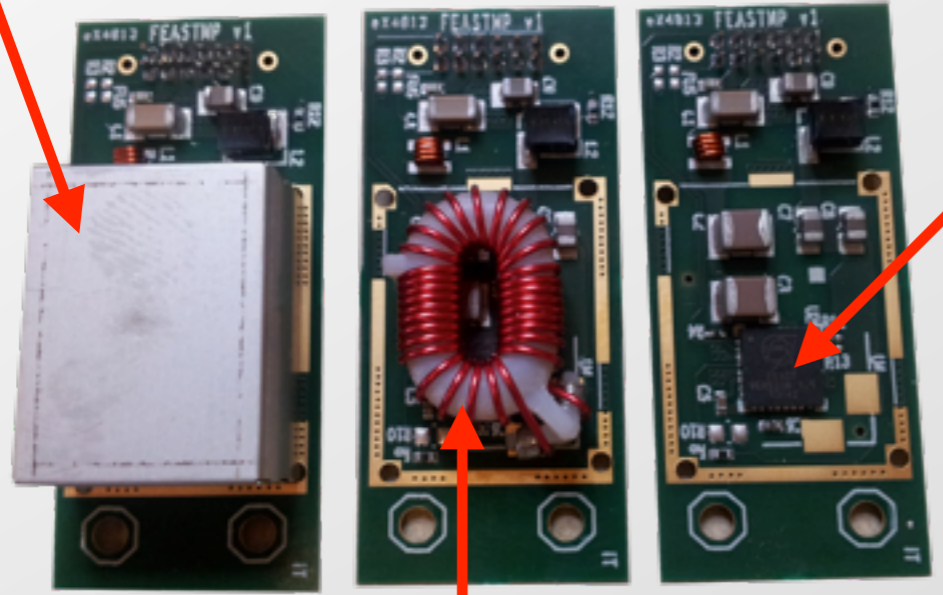
# Architecture of FEAST2: buck converter





Cu shield

**FEASTMP module**



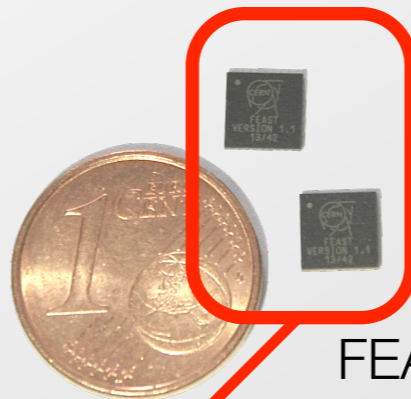
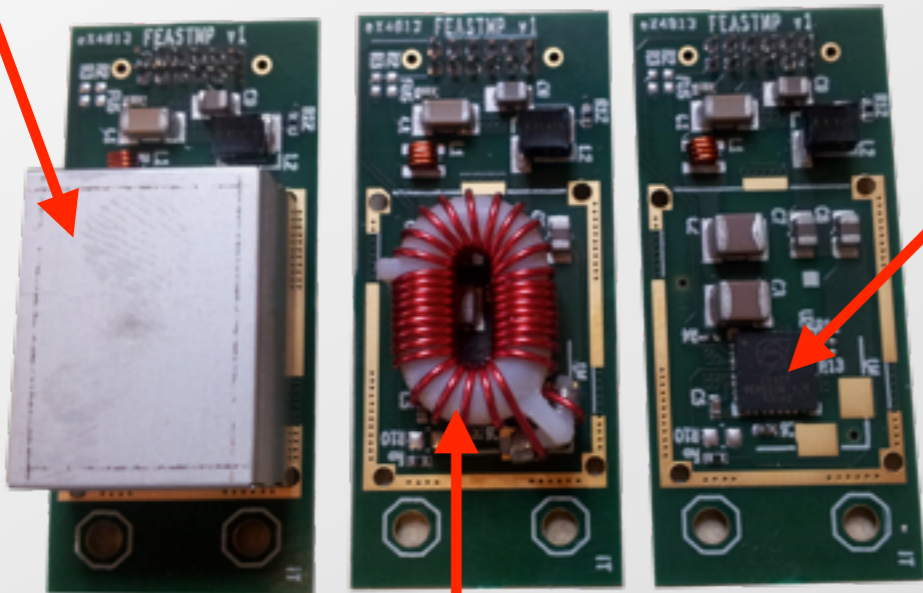
FEAST2 ASIC



Custom air-core toroid inductor, 400nH

Cu shield

### FEASTMP module

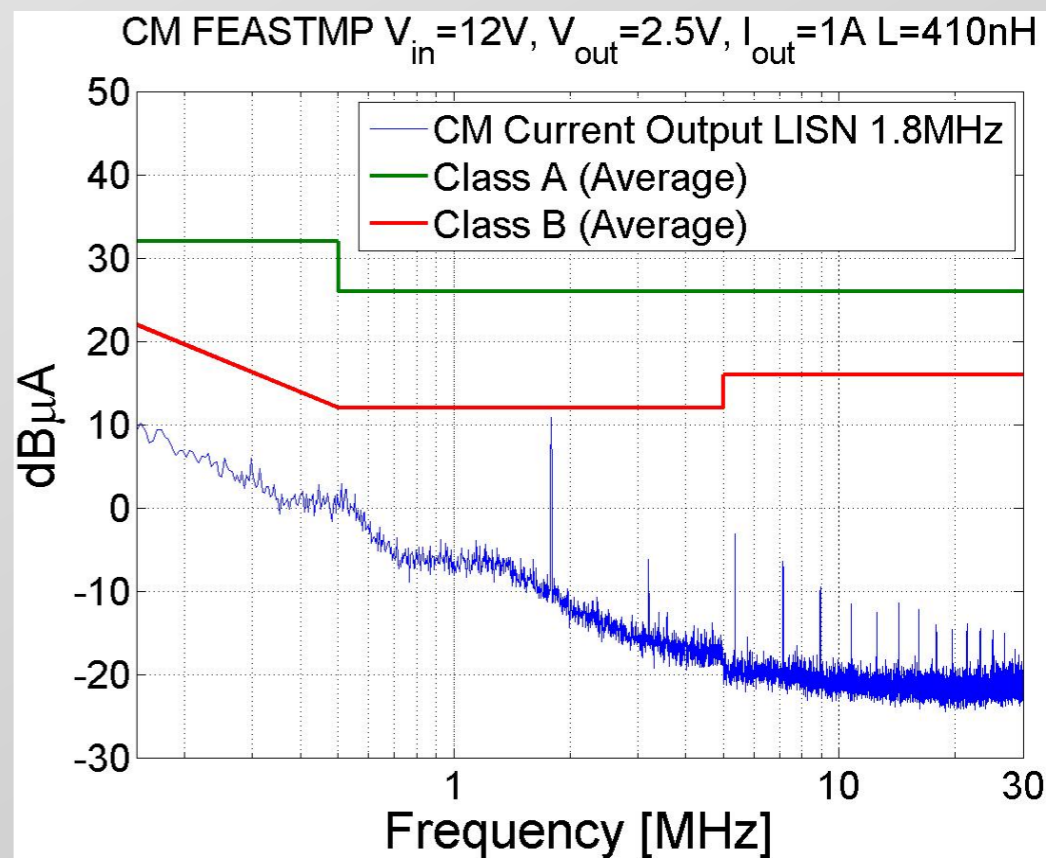


FEAST2 ASIC



Custom air-core toroid inductor, 400nH

### EMC: common mode current noise



# SETs observed during HI irradiation

LET	Cross-section (cm <sup>2</sup> ) for SETs below the nominal V <sub>out</sub>			
	2% bin	6% bin	10% bin	20% bin
	σ (cm <sup>2</sup> ) and duration (μs)	σ (cm <sup>2</sup> ) and duration (μs)	σ (cm <sup>2</sup> ) and duration (μs)	σ (cm <sup>2</sup> ) and duration (μs)
10.2	2.4x10 <sup>-8</sup> (-)			
12.45	9.9x10 <sup>-7</sup> (2.4)		9.8x10 <sup>-7</sup> (-)	
14.42	6.5x10 <sup>-6</sup> (4.1)	9.4x10 <sup>-8</sup> (-)		
17.78		3.3x10 <sup>-7</sup> (-)		
20.4		3.0x10 <sup>-6</sup> (1.6)	1.3x10 <sup>-6</sup> (1.4)	
24.9		6.6x10 <sup>-6</sup> (1.4)	5.0x10 <sup>-6</sup> (1.4)	
32.6		1.0x10 <sup>-5</sup> (2.2)	8.0x10 <sup>-6</sup> (1.5)	1.4E-07 (-)
46.1			9.0x10 <sup>-6</sup> (1.5)	
65.2			8.1x10 <sup>-6</sup> (1.5)	

LET	Cross-section (cm <sup>2</sup> ) for SETs above the nominal V <sub>out</sub>			
	2% bin	6% bin	10% bin	20% bin
	σ (cm <sup>2</sup> ) and duration (μs)	σ (cm <sup>2</sup> ) and duration (μs)	σ (cm <sup>2</sup> ) and duration (μs)	σ (cm <sup>2</sup> ) and duration (μs)
10.2	3.4x10 <sup>-7</sup> (0.5)	7.7x10 <sup>-8</sup> (-)		
12.45	2.7x10 <sup>-6</sup> (1.3)		1.4x10 <sup>-7</sup> (-)	
14.42	5.4x10 <sup>-7</sup> (1.0)	9.4x10 <sup>-8</sup> (-)		
17.78		3.3x10 <sup>-7</sup> (-)		
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32.6		2.3x10 <sup>-6</sup> (1.2)	1.4x10 <sup>-7</sup> (-)	
46.1			1.4x10 <sup>-7</sup> (-)	
65.2			1.4x10 <sup>-7</sup> (0.4)	

Cross-section of SETs observed during heavy ion irradiation, catalogued in amplitude bins. Within each bin, only SETs above (or below) a fixed threshold are counted in the cross-section, and thresholds are expressed in percentages of the nominal V<sub>out</sub> (example: 10% bin thresholds for V<sub>out</sub>=2.5V are 2.25 and 2.75V). In parenthesis, the duration of the SET in μs. Blue figures are limit cross-sections: no SETs have been recorded. LETs are in MeVcm<sup>2</sup>mg<sup>-1</sup> and have been obtained using the following ions: Ar at 0, 35, 45 and 55° incidence, Ni at 0 and 35° incidence and Kr at 0, 45 and 65° incidence.